

FIG. 1A

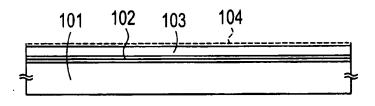
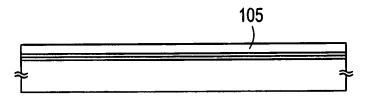


FIG. 1B



approved Le

FIG. 1C

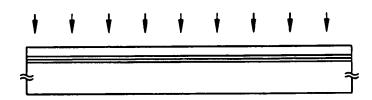
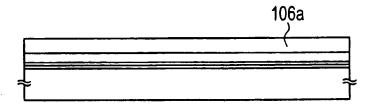


FIG. 1D





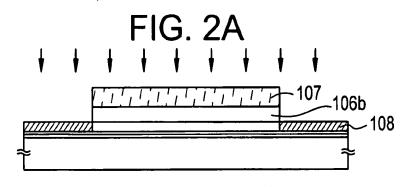


FIG. 2B

approved Lee

16:

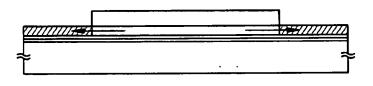


FIG. 2C

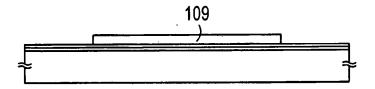
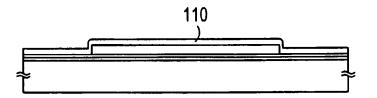
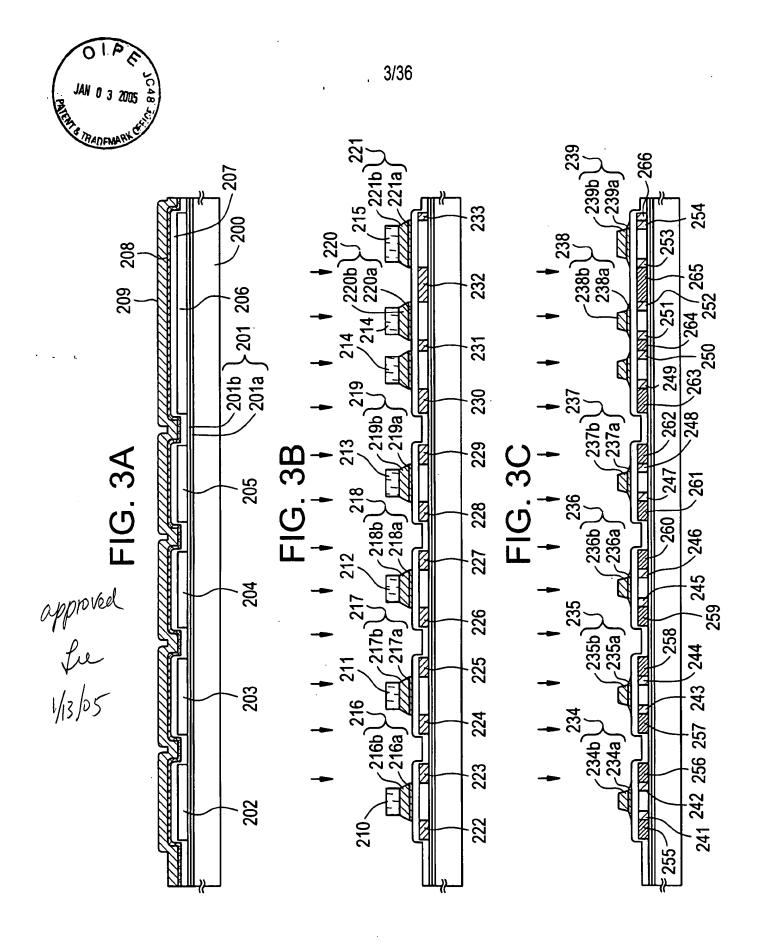
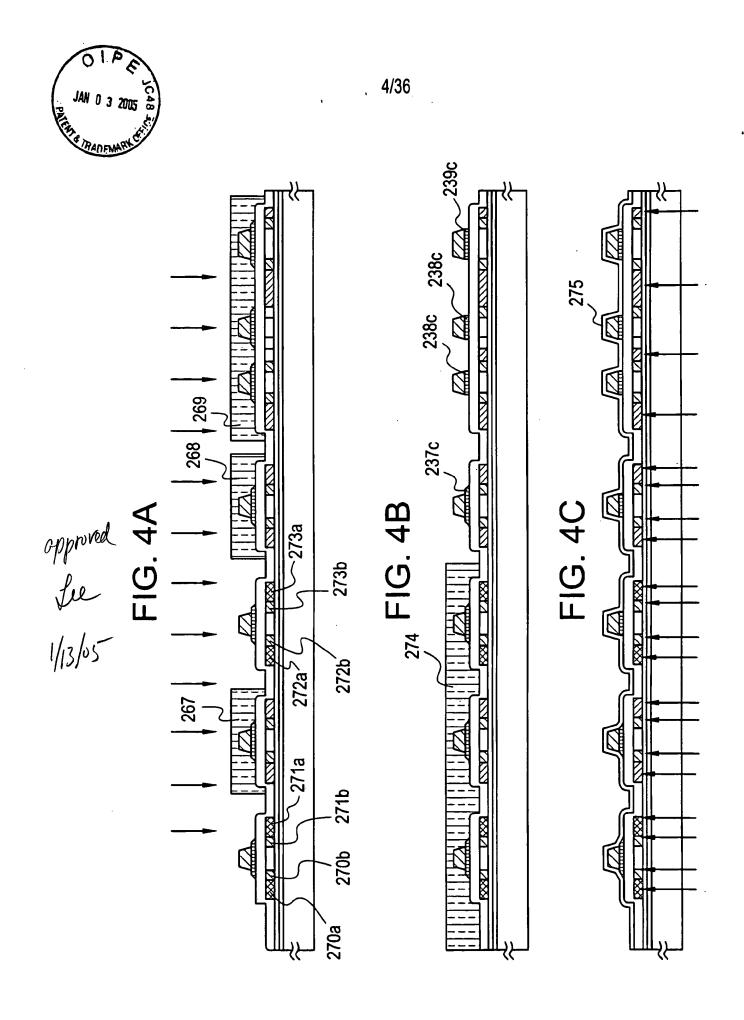


FIG. 2D

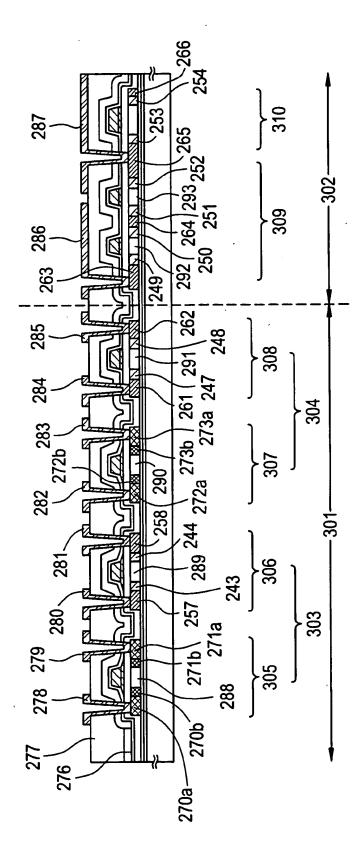








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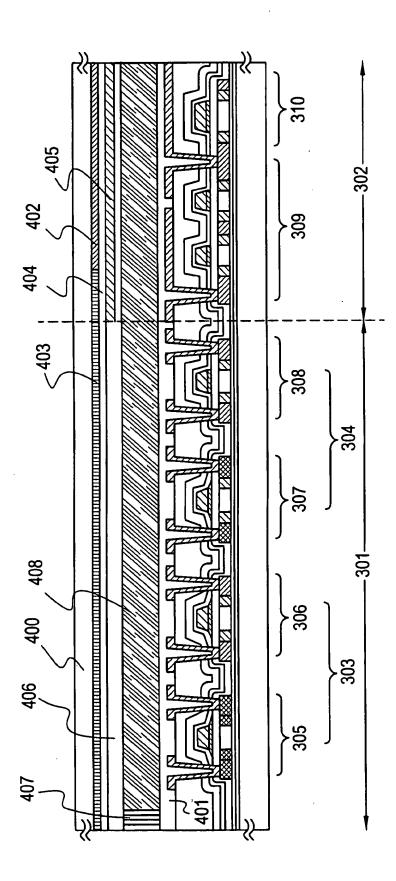




FIG. 7

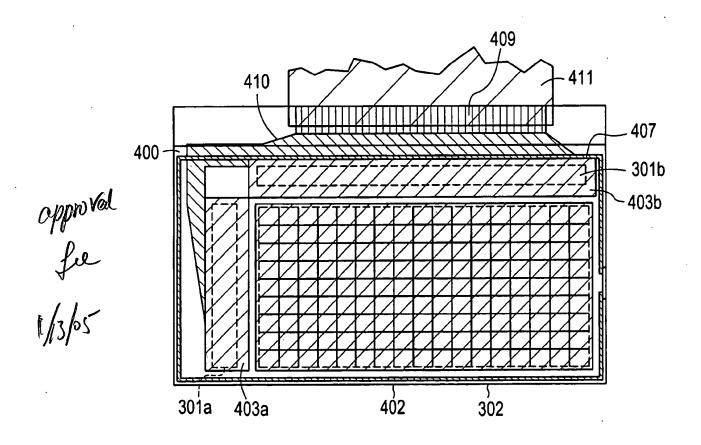
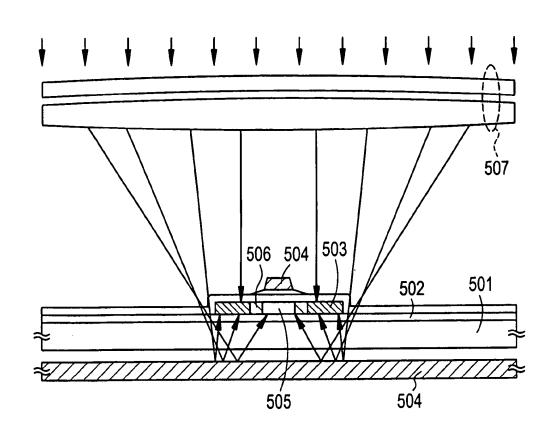


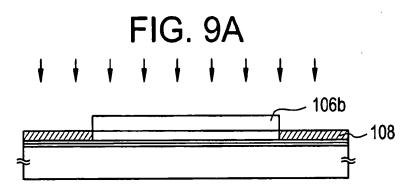


FIG. 8









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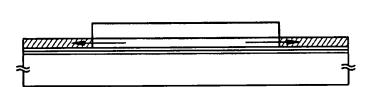
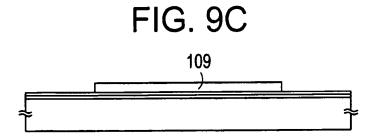
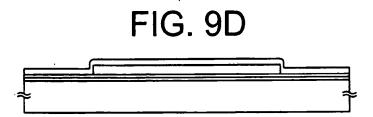


FIG. 9B







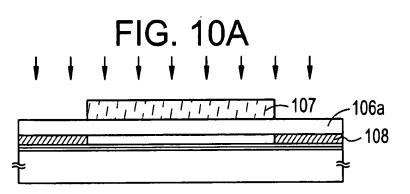


FIG. 10B

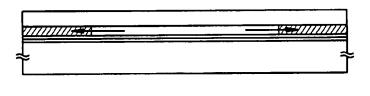


FIG. 10C

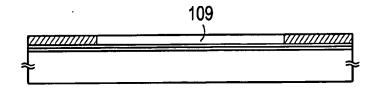
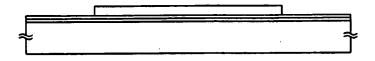


FIG. 10D



approved Le 1/13/25



FIG. 11A

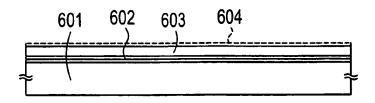
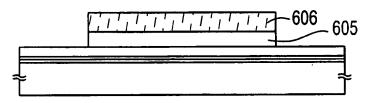


FIG. 11B



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FIG. 11C

FIG. 11D

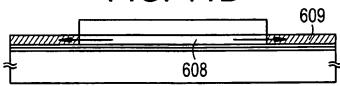
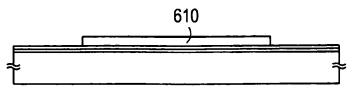


FIG. 11E





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FIG. 12A

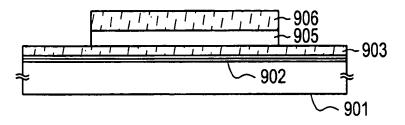


FIG. 12B

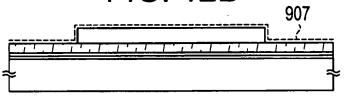
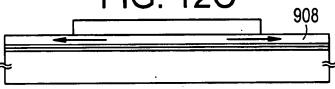


FIG. 12C



approved Lee

FIG. 12D

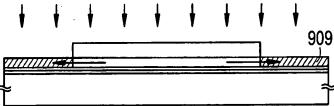


FIG. 12E

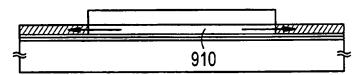
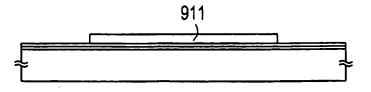


FIG. 12F





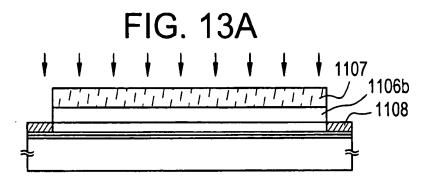


FIG. 13B



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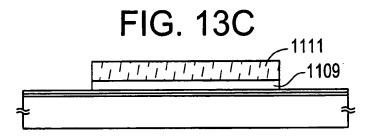
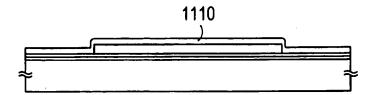


FIG. 13D



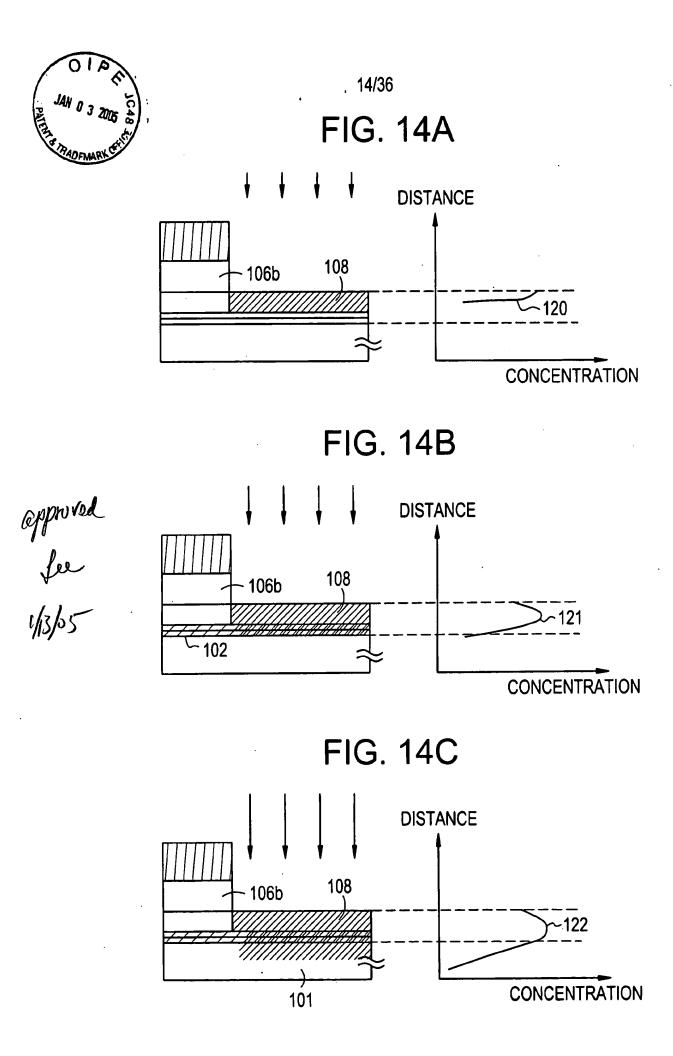




FIG. 15

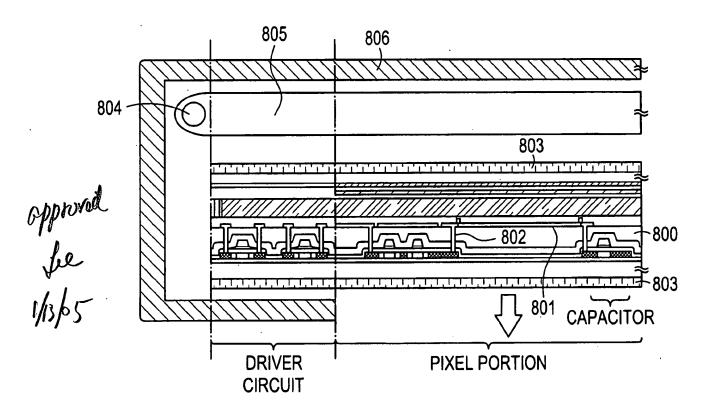
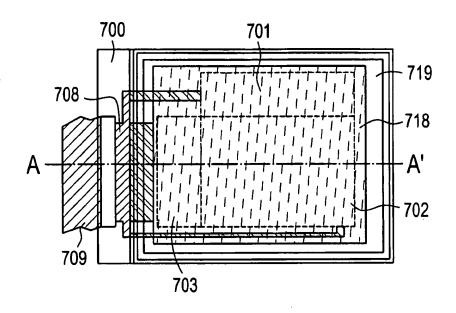




FIG. 16A



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FIG. 16B

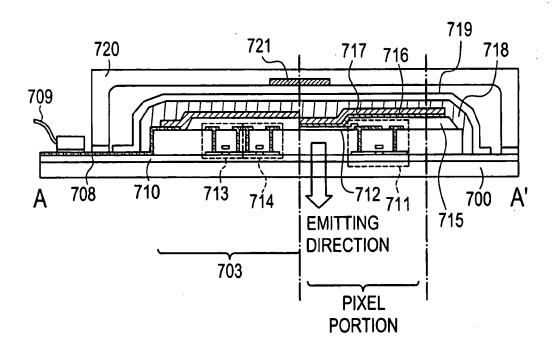




FIG. 17

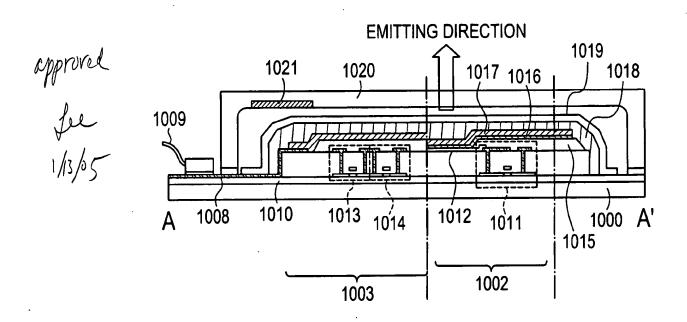




FIG. 18



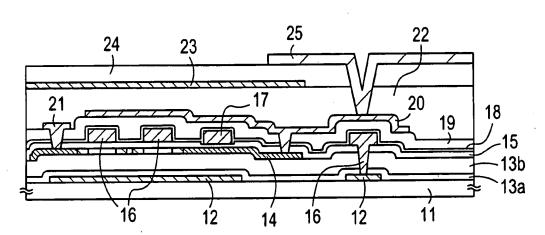
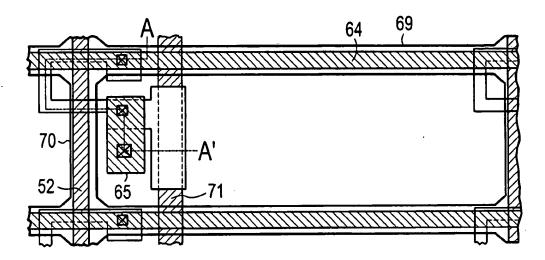




FIG. 19A



approved Lee

FIG. 19B

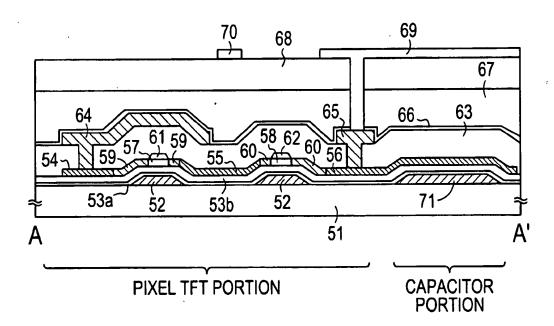




FIG. 20

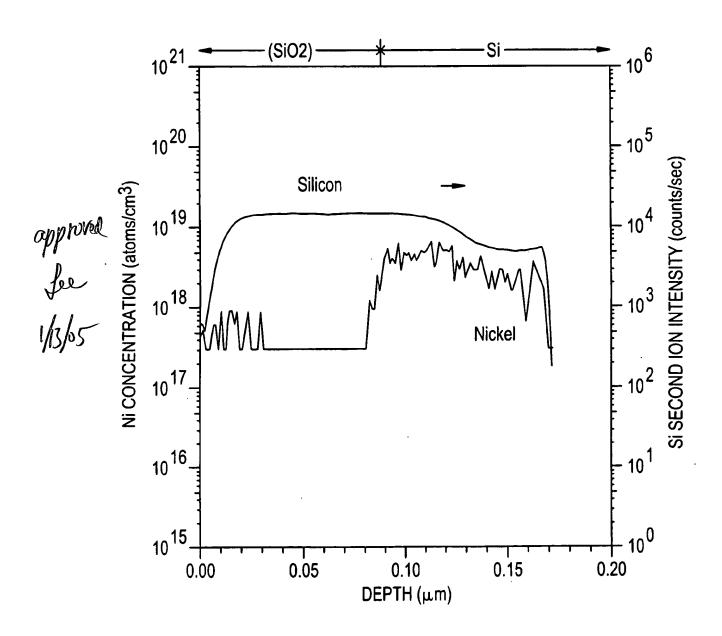




FIG. 21

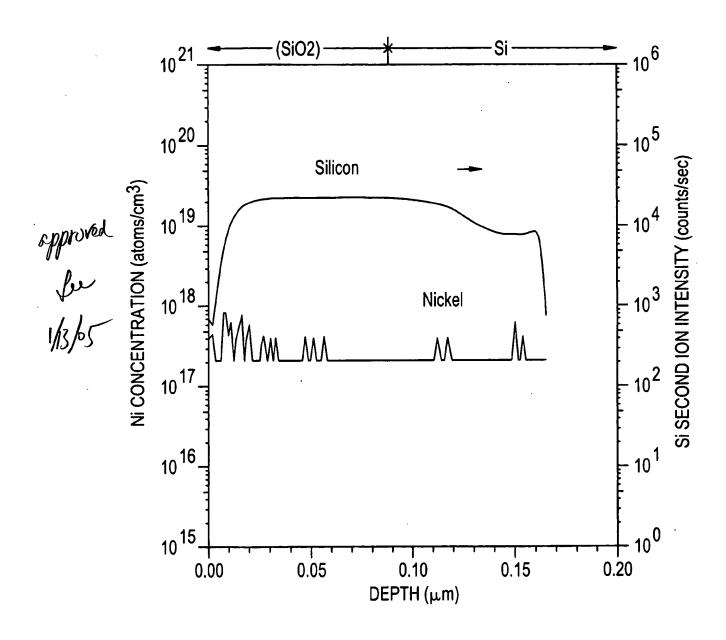




FIG. 22

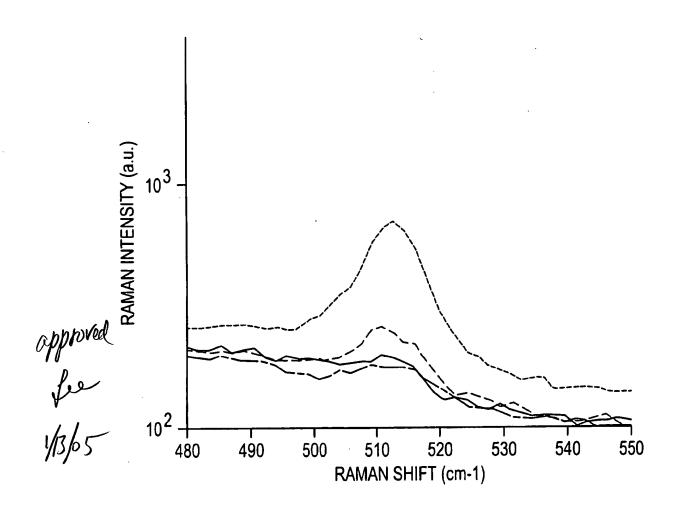




FIG. 23

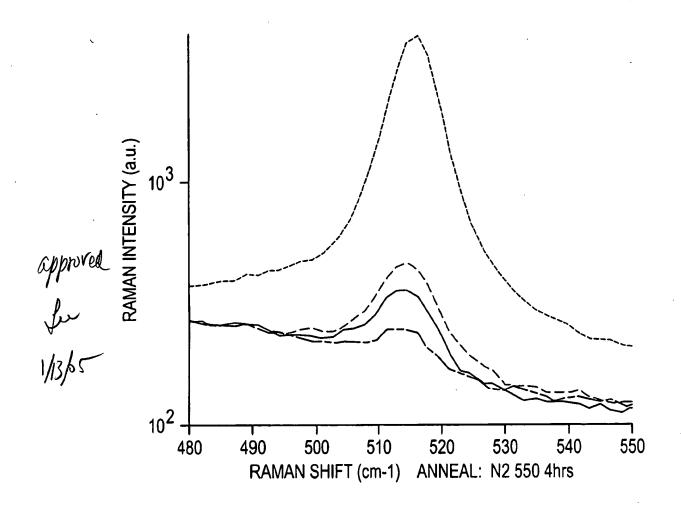
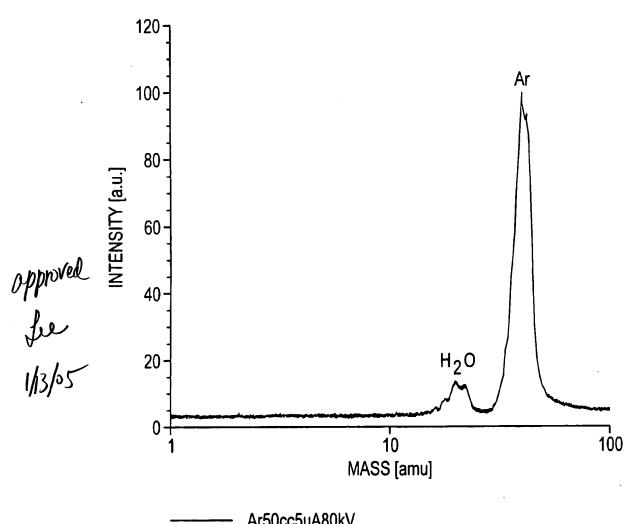




FIG. 24



Ar50cc5uA80kV

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FIG. 29

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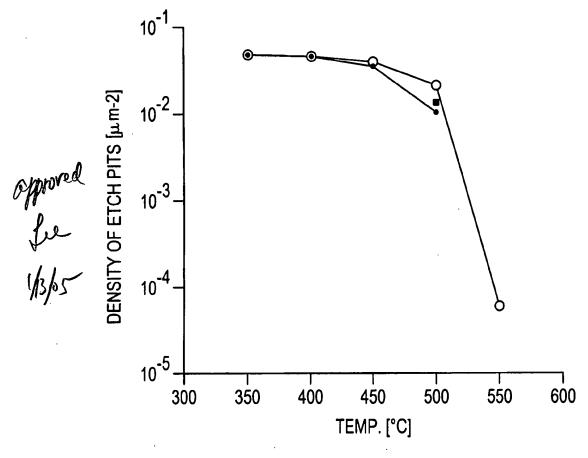
_	L LE			S S			_	֡֓֡֓֓֓֜֓֓֓֓֓֓֓֓֓֓֓֓֓֓֓֓֓֓֓֓֓֓֓֓֡֓֓֓֓֓֡֜֓֓֓֡֡֓֡֓֡֓֓֡֓
		1. 0E-06-	- 100		Mary May Mary Language Mary Mary Mary Mary Mary Mary Mary Mary	0 -15 -10 -5 0 5 10 15 20	\(\)\(\)\(\)\(\)	

AP005_CN			MEASUREMENT	13	2	ULATION	z	7.0	4.1 115	ATION						
	CHNSA311	SemiAuto	유 -	i.	ber	PARAMETER OF CALCULATION	TYPE		W [#iii] DIELECTRIC CONSTANT THICKNESS OF OXIDE	RESULT OF CALCULATION	2.34E-04	3.70E-12	0.231	1.222	0.175	179.9
Lot No.:	FILE NAME	Comment	PARAMETER	VD start VD sten	VD step number	PARAMET	CHANNEL TYPE	L [µm]	W [pmi] DIELECTRIC CONSTAN THICKNESS OF OXIDE	RESUL	lon_2 [A]	loff_2 [A]	Shift_1[V]	\$∑	S-value [V/dec]	μFE (max) [cm2/Vs]
						•	•			f	1 _					



FIG. 26

Ar dope 80kV 5E15 (into GI900 A/poly-Si500 A/SiON + SiNO/#1737)

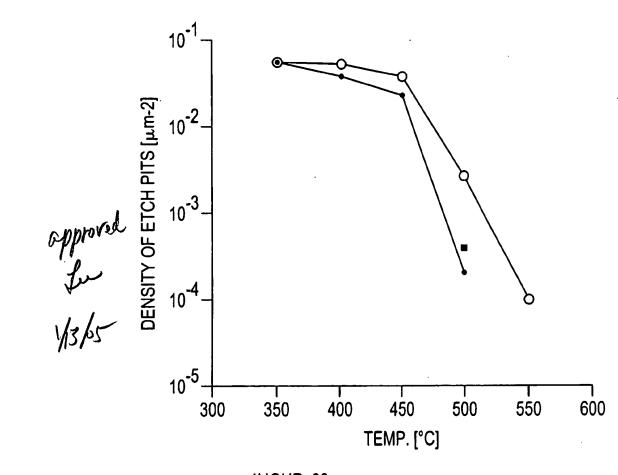


- 6HOUR
- → 8HOUR



FIG. 27

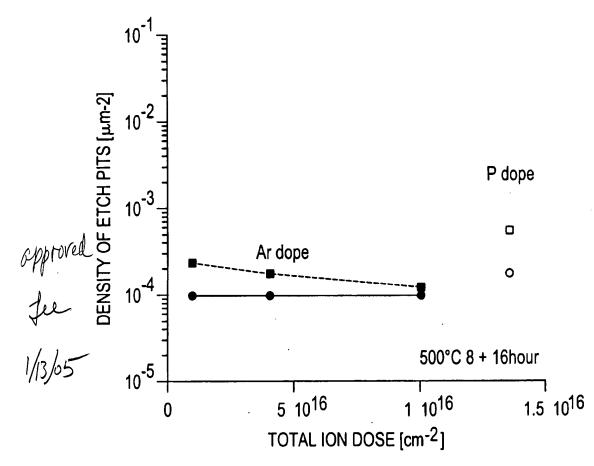
Ar dope 80kV 5E15 (into GI900 A/poly-Si500 A/SiON + SiNO/#1737)



- --O- 4HOUR 30μm
- 6HOUR
- → 8HOUR



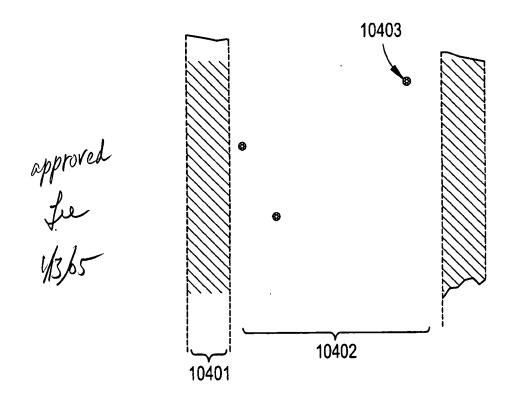
FIG. 28

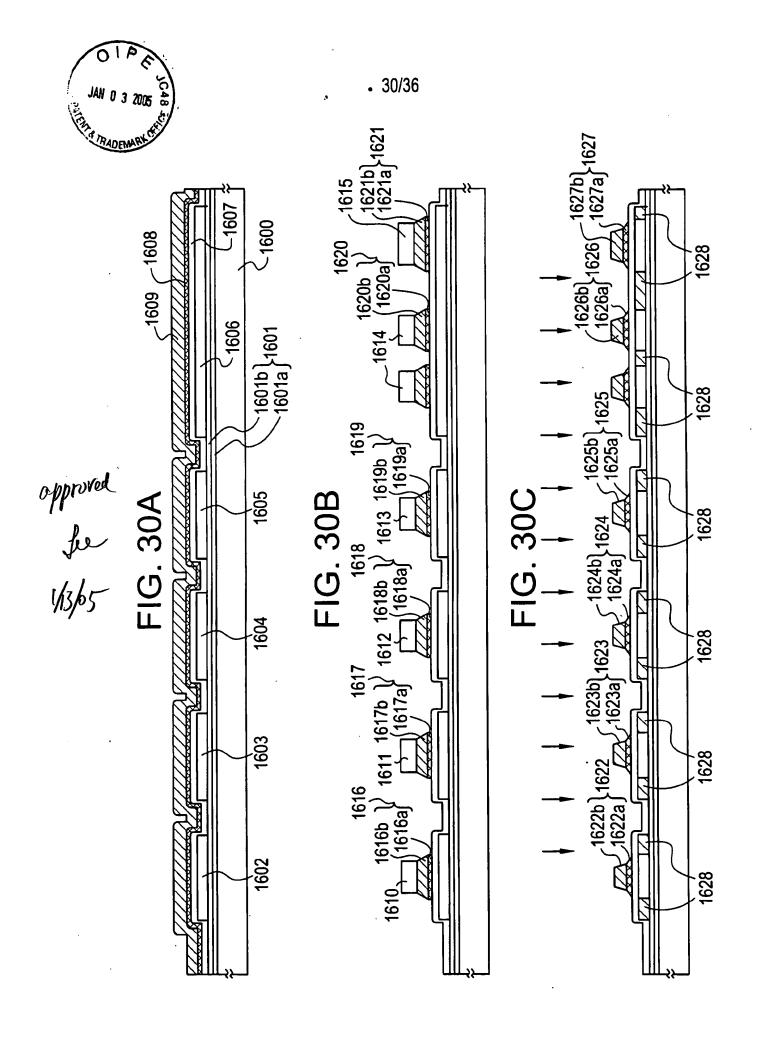


■. □: 50μm ●. ο: 30μm

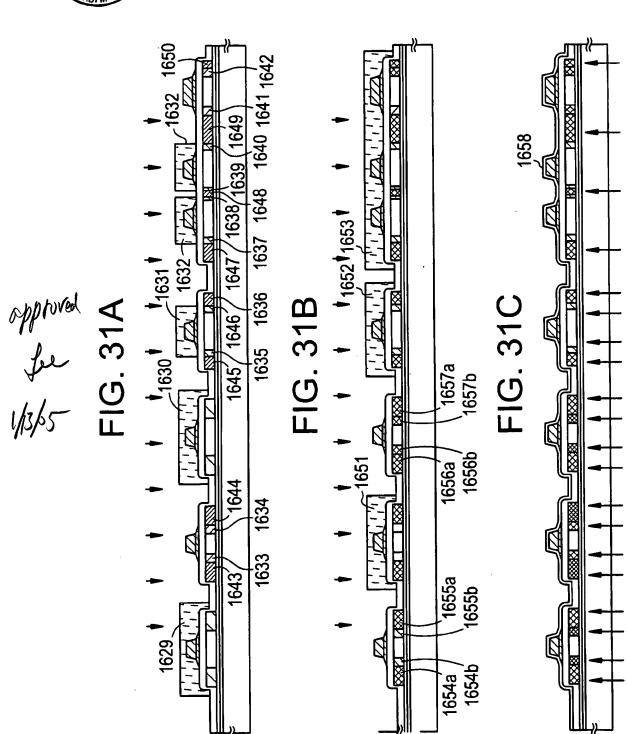


FIG. 29

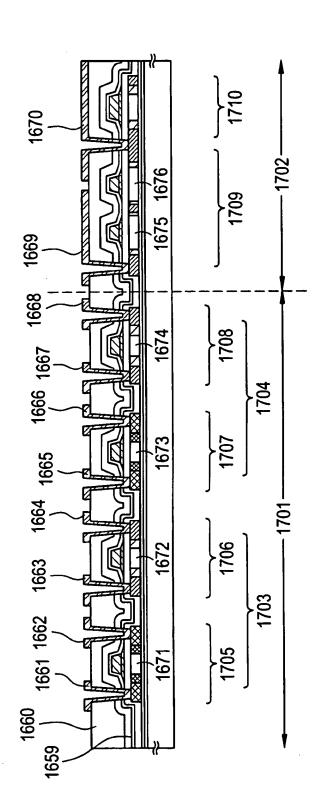












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FIG. 33A

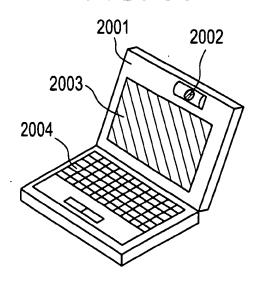


FIG. 33B

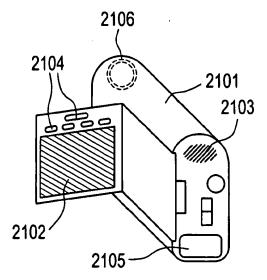


FIG. 33C

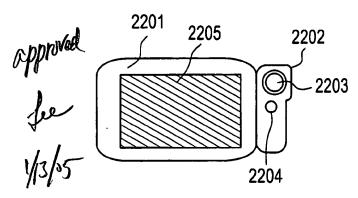


FIG. 33D

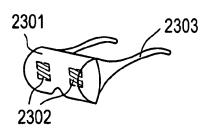


FIG. 33E

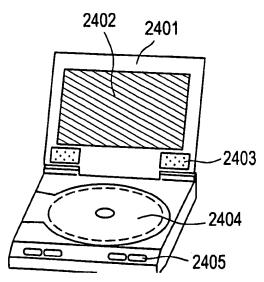


FIG. 33F

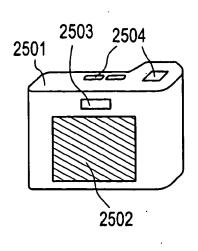


FIG. 34C

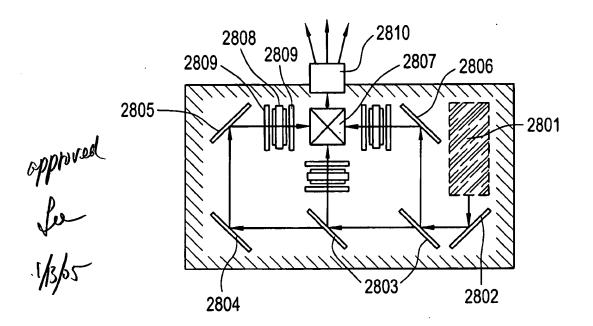
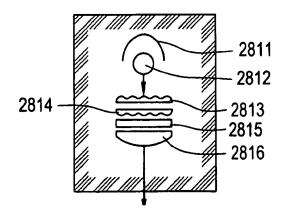
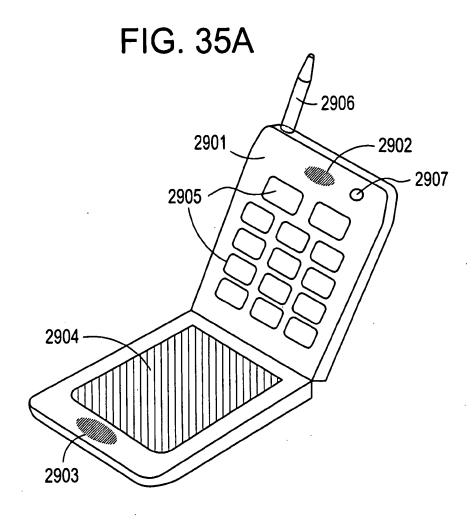


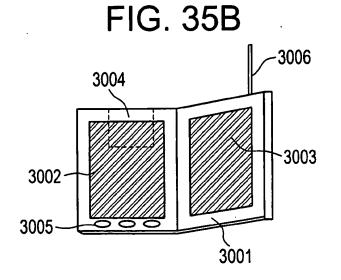
FIG. 34D







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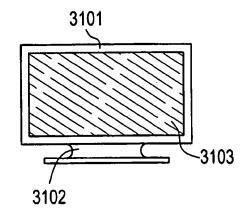




FIG. 36

GETTERING CONDITION

MAGNIFICATION

550° C4hrs

X 200

approved for